

Sheet 1 of 1  
**IAP5 Rec'd PCT/PTO 28 SEP 2006**  
 10/594,846

Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 28953.2004	Application No. 10/594,846
<b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)		Applicant Makoto Iwai et al	
(37 CFR §1.98(b))		Filing Date 11/08/2006 <del>Herewith</del>	Group Art Unit 1792

### U.S. Patent Documents

Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
/F.H./	AA	6,949,140	9/2005	Sarayama et al	117	81	
/F.H./	AB	6,398,867	6/2002	D'Evelyn et al	117	11	

### Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publn. Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
/F.H./	AC	2002-293696	10/2002	Japan			Abstract	
/F.H./	AD	2003-292400	10/2003	Japan			Abstract	
/F.H./	AE	2003-511326	3/2003	Japan			X	
/F.H./	AF	2005-8444	1/2005	Japan			Abstract	
/F.H./	AG	WO2004/013385	6/2003	WIPO			Abstract	
/F.H./	AH	WO01/024921	9/2000	WIPO				
	AI							
	AJ							
	AK							
	AL							
	AM							
	AN							
	AO							

### Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
/F.H./	AP	Kawamura, F. et al, "Growth of a Large GaN Single Crystal Using the Liquid Phase Epitaxy (LPE) Technique," Jpn. J. Appl. Phys., Vol. 42 (2003), pp. L4-L6
	AQ	
	AR	
	AS	
	AT	

Examiner Signature /Felisa Hiteshew/	Date Considered 04/11/2008
---	-------------------------------

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /F.H./

Disclosure Form (PTO-1449)